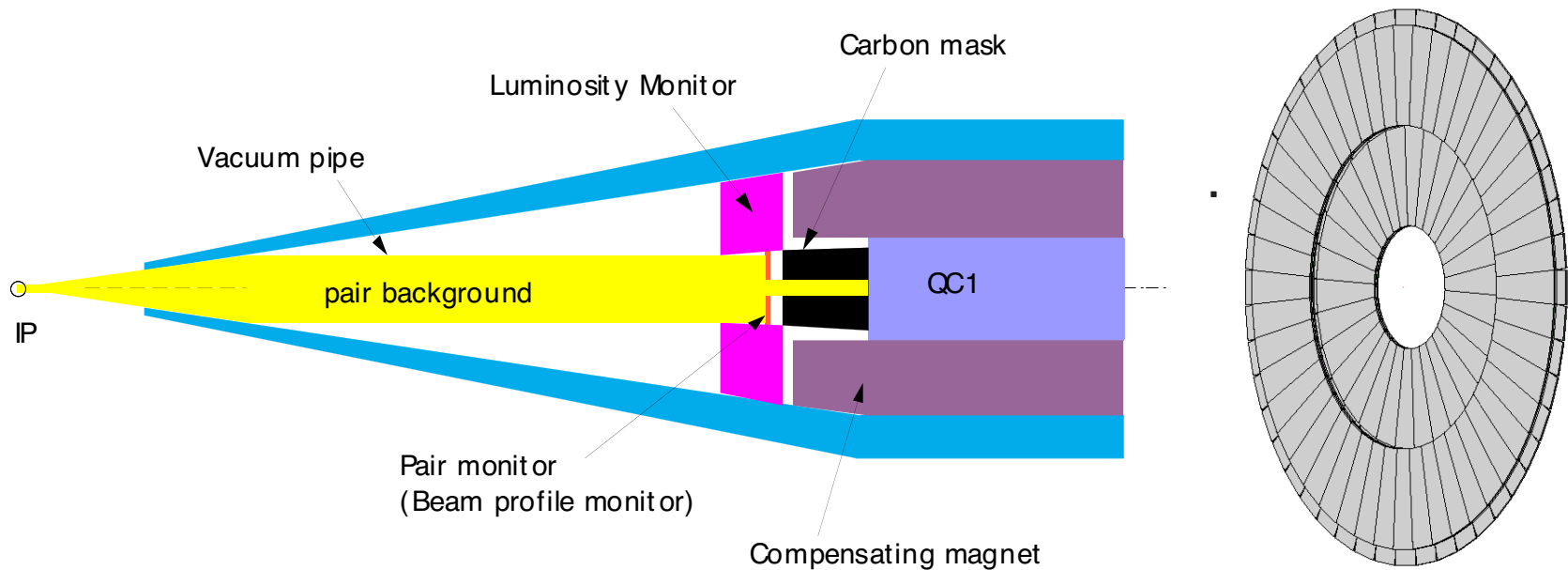


# Beamprofile Monitor R&D based on 3D Sensor

Collaboration of  
Brunel, Hawaii, KEK, Stanford, Tohoku

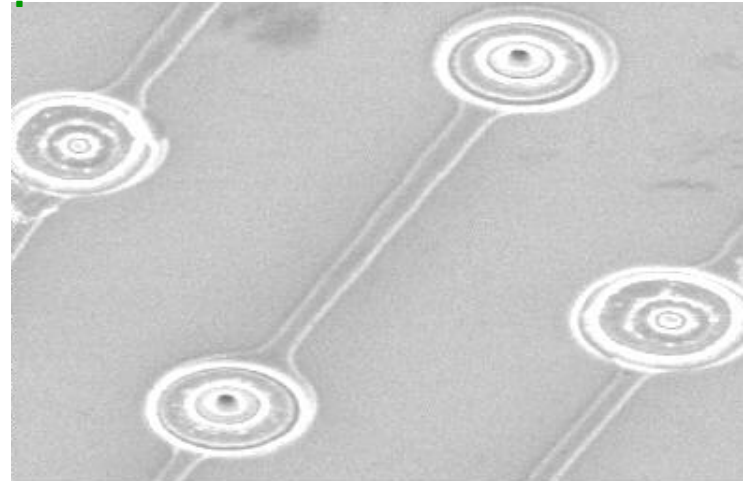
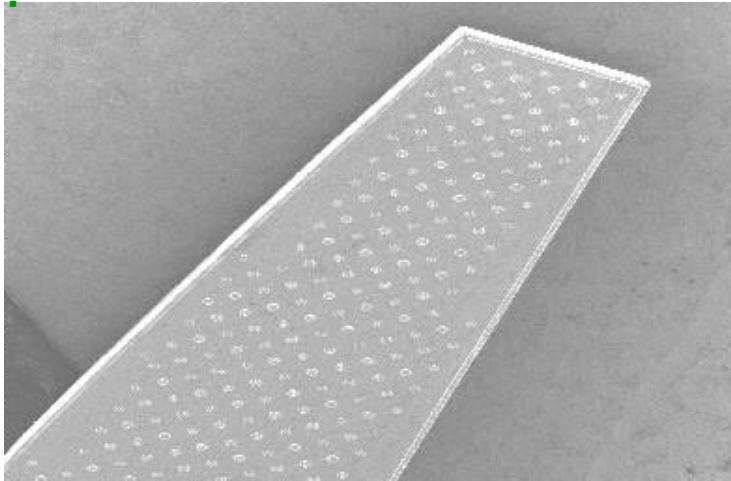
Presented by: Hitoshi Yamamoto  
(Tohoku University)

LCWS Paris, April 20, 2004.



**Outer radius  $\sim 8\text{cm}$ . One on each side of IP.  
Trapezoidal sensors desirable.**

# Fabrication of 3D pixel sensor



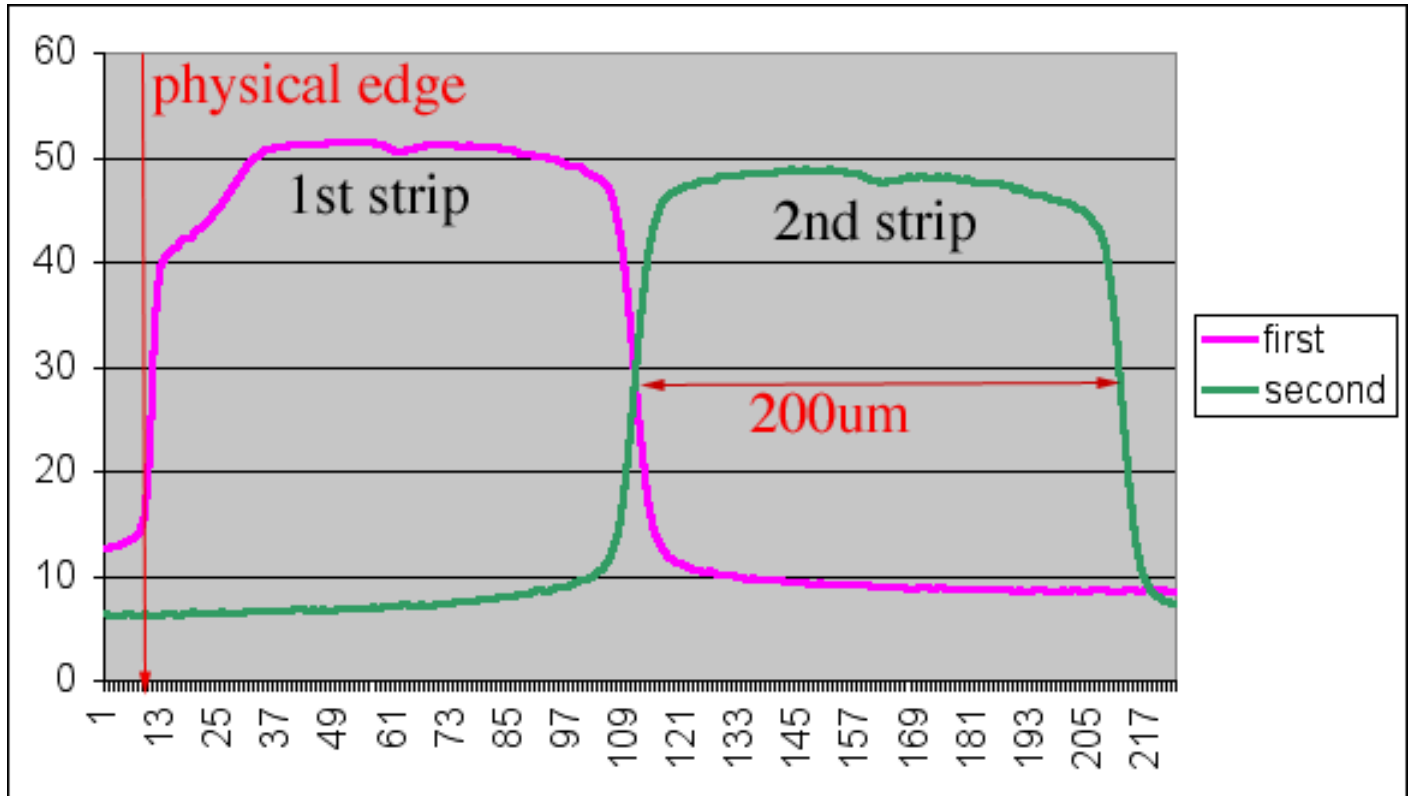
1. Fabricated by S. Parker et. al., at CIS, Stanford).
2. Trapezoidal shape possible for disk or cone.  
( $180\mu\text{m}$  thick,  $200\mu\text{m}$  readout pitch, 3mm long)
3. Fabrication completed and being tested at LBL and Tohoku.

# X-Ray Test (rectangular version)

Goal: establish dead region at electrodes and edges

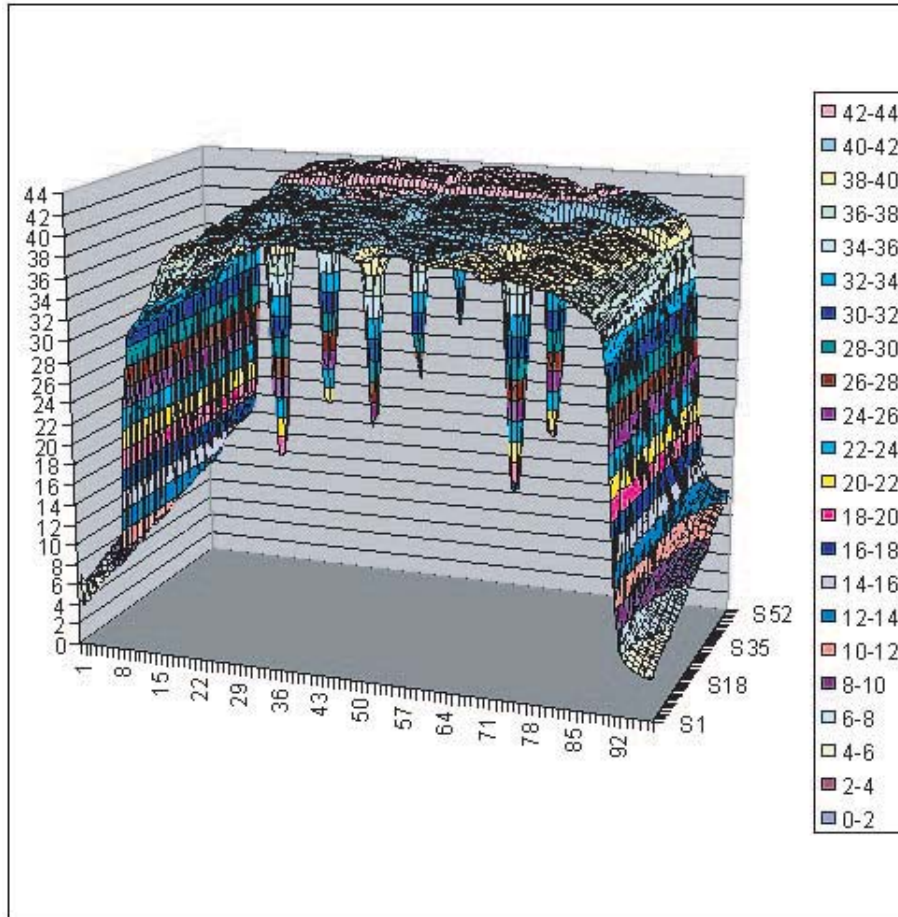
- 180  $\mu\text{m}$  thick, 200  $\mu\text{m}$  readout pitch
- Connected as strips for testing
- ALS (Advanced Light Source) at LBL
- 12 keV synchrotron X-rays  
(penetrates Aluminum metal layers)
- Focused to  $\sim 2\mu\text{m}$  spot size by ellipsoidal X-ray mirrors
- Measure the currents out of strips directly

## Strip currents on 1st and 2nd strips



Dead region near edge  $2 \pm 2\mu\text{m}$

## Dead region near electrodes



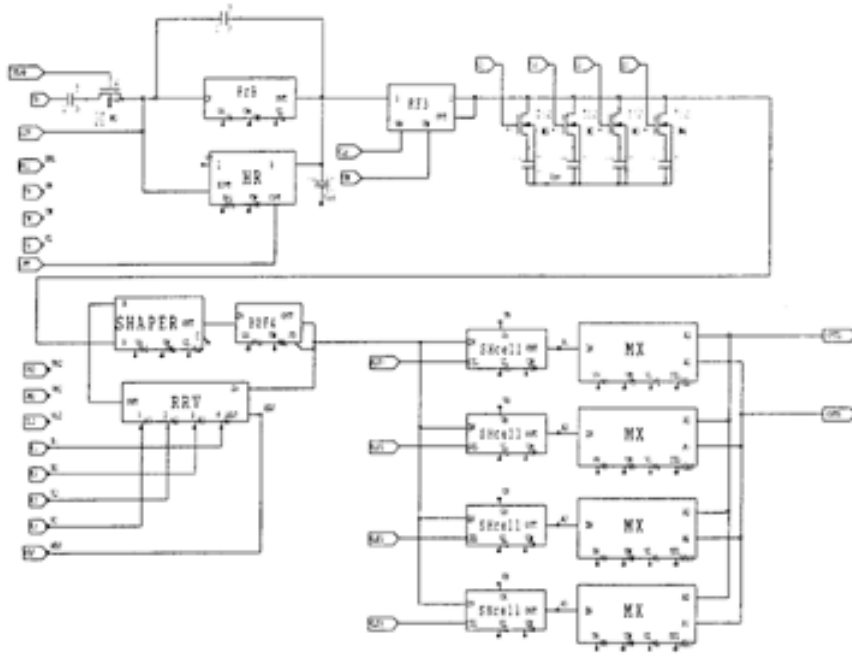
Current on any strip vs X-ray position (unit:  $2\mu\text{m}$ )

# Pixel Readout Chip Prototype.

1. Circuit design by KEK and Tohoku.
2. SPICE Simulation study by Tohoku.
3. VLSI layout by a company in Hiroshima.
4. Submitted to VDEC (Rohm  $0.35\mu\text{m}$ ).
5. Delivered on Jan 20, 2003.
6. Tested at Tohoku.
7. Modifications in design ready for submission.

# Readout electronics

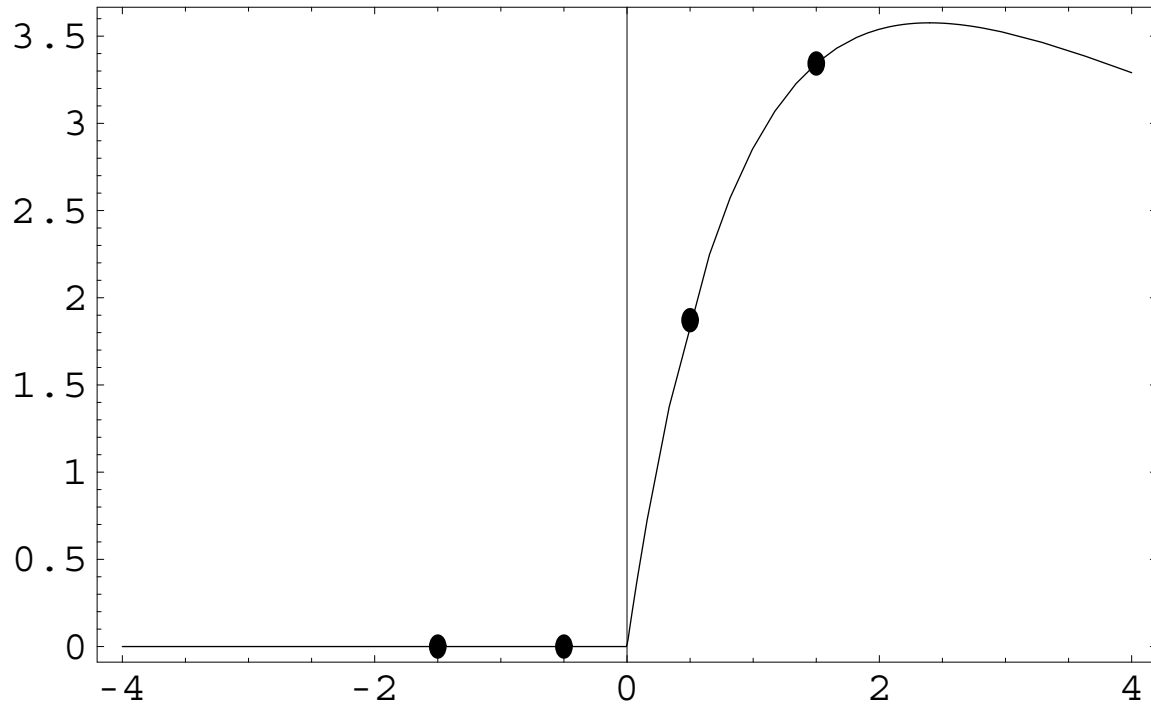
## Block diagram of the circuit



- 32ch per chip (prototype)
- Preamp → RC filter  
→ Voltage amp. shaper  
→ Sample and Hold
- 4 samplings →  
time and pulseheight
- Serial output of 4 vals/ch.  
as a step function.
- All functions verified.



# Timing measurement by 4 sample-and-holds 500 ns apart



Fit the parametrized function  $\rightarrow$  time and pulse height.

## Reconstruction of the hit time

$$v_1 = A \left( 1 - \exp\left(-\frac{t_1 - t_0}{\tau}\right) \right) e^{-\frac{t_1 - t_0}{T}}$$

$$v_2 = A \left( 1 - \exp\left(-\frac{t_2 - t_0}{\tau}\right) \right) e^{-\frac{t_2 - t_0}{T}}$$

$\tau = RC$  : time constant of the rise time.

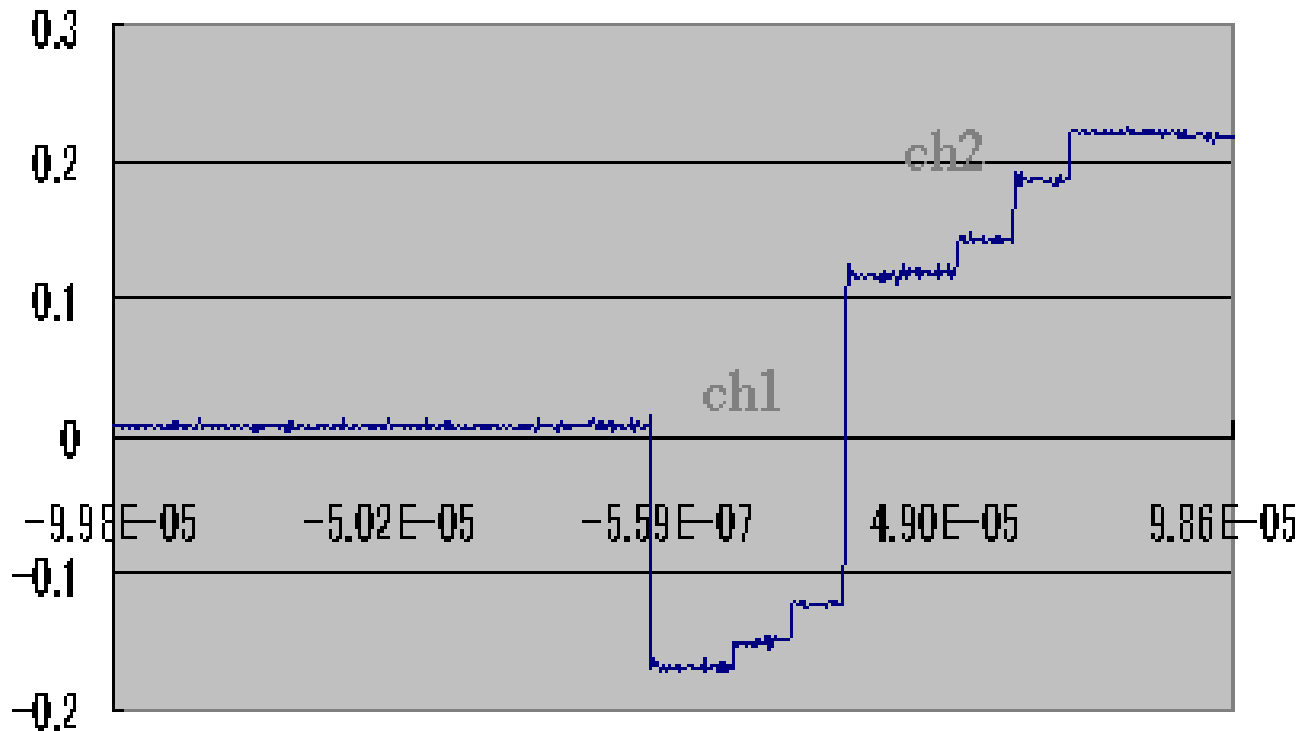
$T$ : time constant of the decay time.

$$t_0 = \tau \log \frac{v_2 - v_1}{v_2 \exp\left(-\frac{t_1}{\tau}\right) - v_1 \exp\left(-\frac{t_2}{\tau}\right)}$$

Then the pulseheight  $A$  can also be reconstructed.

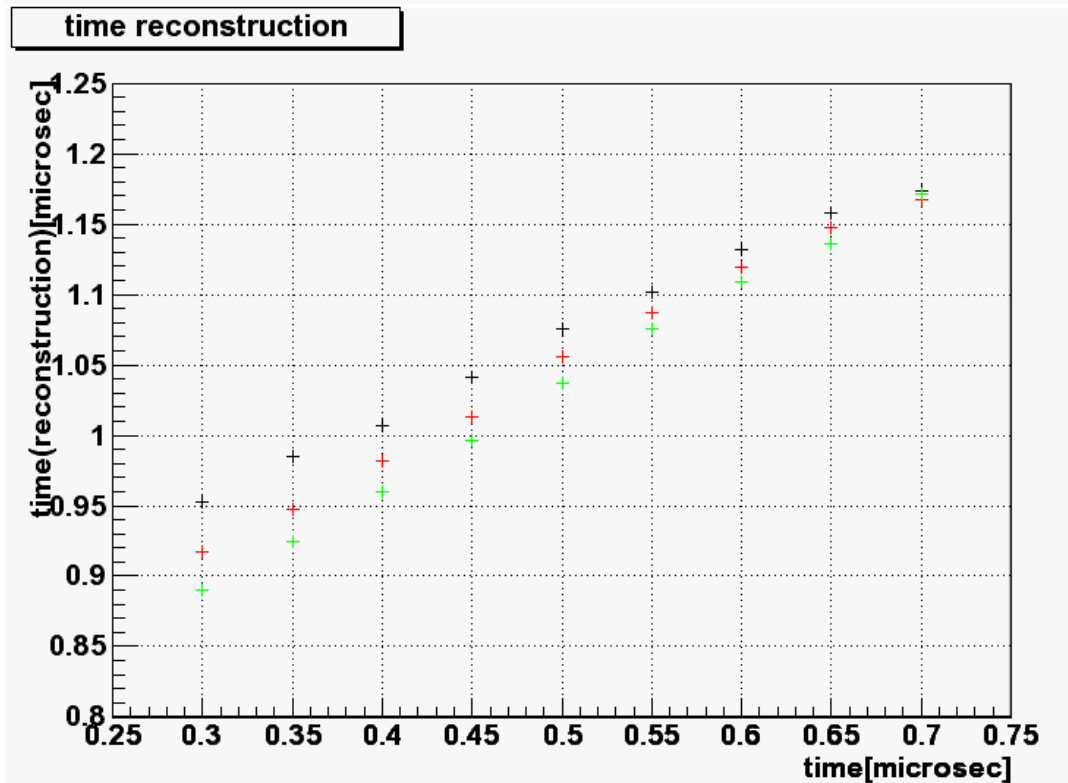
$$A = \frac{v_1}{\left( 1 - \exp\left(-\frac{t_1 - t_0}{\tau}\right) \right) e^{-\frac{t_1 - t_0}{T}}}$$

## Serial readout output



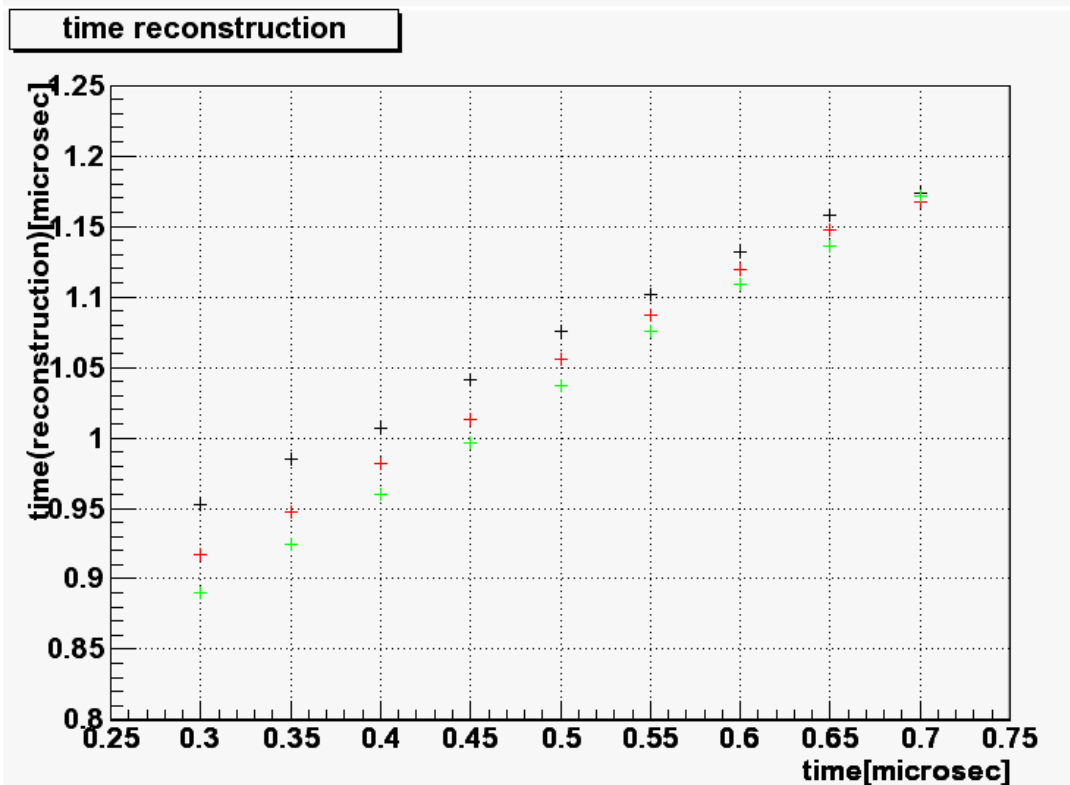
**Large offsets for each channel observed.  
Some channels saturated.**

# Time reconstruction (test pulse injection)



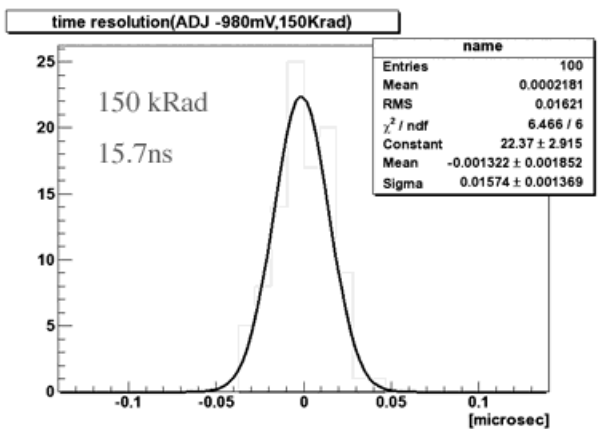
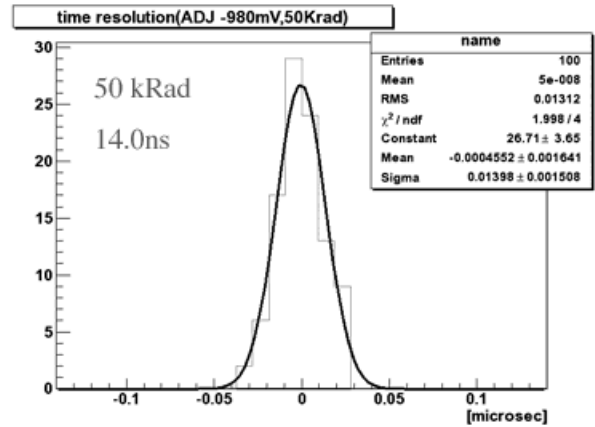
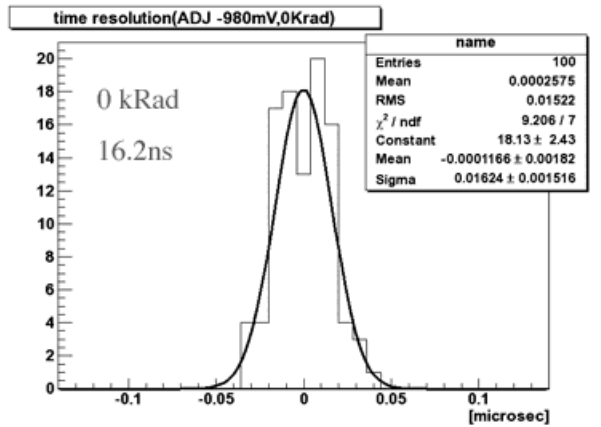
$\blackplus$ :  $\tau = 0.3 \mu\text{s}$ ,  $\color{red}\blackplus$ :  $\tau = 0.5 \mu\text{s}$ ,  $\color{green}\blackplus$ :  $\tau = 0.8 \mu\text{s}$

# Pulse height reconstruction (test pulse injection)



$\times$ :  $\tau = 0.3\mu\text{s}$ ,  $\times$ :  $\tau = 0.5\mu\text{s}$ ,  $\times$ :  $\tau = 0.8\mu\text{s}$   
Find the effective  $\tau$  that works.

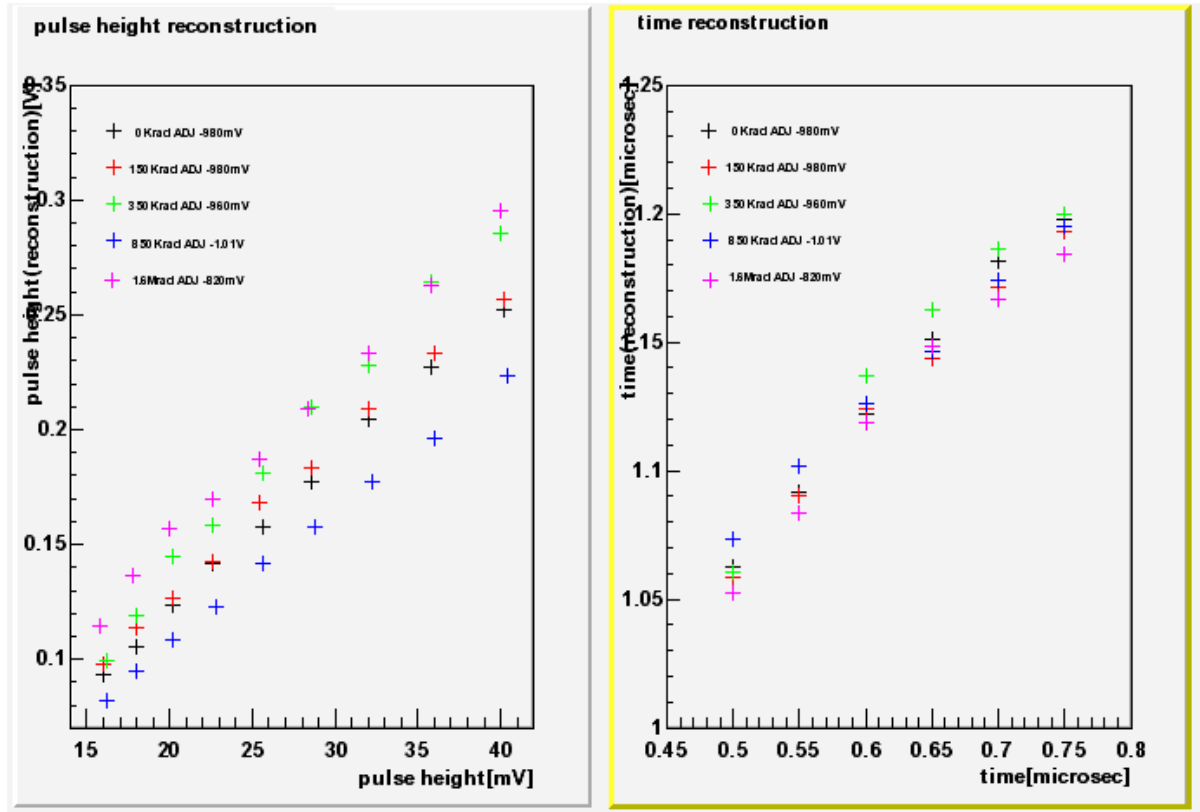
# Time resolution



# Radiation test (Co60)

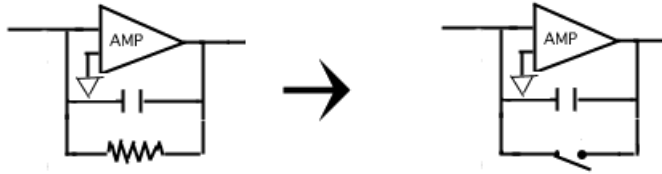
(2 MRad/yr expected close to the beam.)

Withstands up to (at least) 1.8 MRad



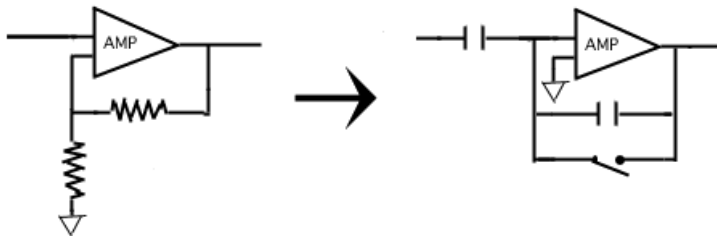
## Modification of the circuit

### Preamp



Removes uncertainty of time constant.  
Possibly better time (and pulse height) resolution.

### Output amp



Hope to reduce the channel-dependent offset.

→ Submitting to VDEC



## Next Steps

1. Fabrication of the modified circuit.
2. Tests of the modified chips.
3. Shrink the size.
4. Noise tolerance.